

METHOD OF FABRICATING A BIPOLAR JUNCTION TRANSISTOR

Abstract

A substrate with a plurality of isolation structures for defining at least an active area thereon is provided. Ions of a first conductive type are implanted into the substrate to form a doping region in the active area. Following that, a protective layer is formed on the substrate, the protective layer having an opening to expose the doping region. A first doping layer of a second conductive type and a second doping layer of the first conductive type are formed on the doping region, respectively, to complete fabrication of a bipolar junction transistor.